2SA1127

Silicon PNP epitaxial planar type

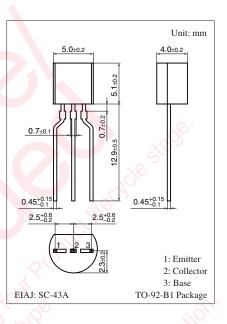
For low-frequency and low-noise amplification Complementary to 2SC2634

Features

- Low noise voltage NV
- \bullet High forward current transfer ratio h_{FE}

Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V _{CBO}	-60	V				
Collector-emitter voltage (Base open)	V _{CEO}	-55	V				
Emitter-base voltage (Collector open)	V _{EBO}	-7	v				
Collector current	I _C	-100	mA				
Peak collector current	I _{CP}	-200	mA				
Collector power dissipation	P _C	400	mW				
Junction temperature	Tj	150	°C				
Storage temperature	T _{stg}	-55 to +150	°C				
			10				





Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

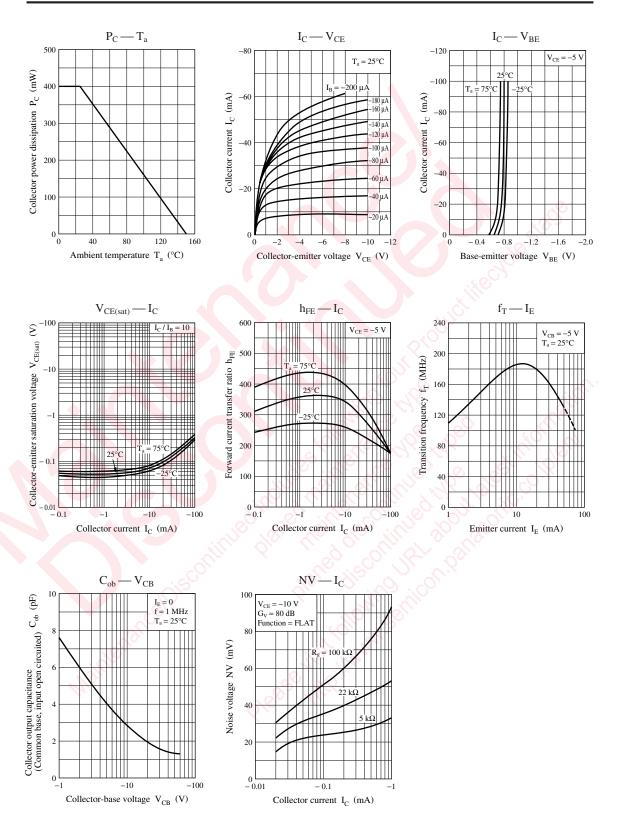
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$	-60	S		V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -1 {\rm mA}, I_{\rm B} = 0$	-55	0		V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -10 \ \mu A, I_{\rm C} = 0$	-7			V
Base-emitter voltage	V _{BE}	$V_{CE} = -1 V, I_C = -30 mA$			-1	V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$		-1	-100	nA
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -10 \text{ V}, I_B = 0$		- 0.01	-1.00	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = -5 \text{ V}, I_C = -2 \text{ mA}$	180		700	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -10 \text{ mA}$			- 0.6	V
Transition frequency	f _T	$V_{CB} = -5 \text{ V}, I_E = 2 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Noise voltage	NV	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}, G_V = 80 \text{ dB}$			150	mV
		$R_g = 100 \text{ k}\Omega$, Function = FLAT				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	S	Т
h _{FE}	180 to 360	260 to 520	360 to 700

Panasonic



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